XC7SH02

2-input NOR gate
Rev. 01 — 7 September 2009

Product data sheet

1. **General description**

XC7SH02 is a high-speed Si-gate CMOS device. It provides a 2-input NOR function.

Features 2.

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - ◆ MM JESD22-A115-A: exceeds 200 V
 - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

Type number	Package	Package						
	Temperature range	Name	Description	Version				
XC7SH02GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				
XC7SH02GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				



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2-input NOR gate

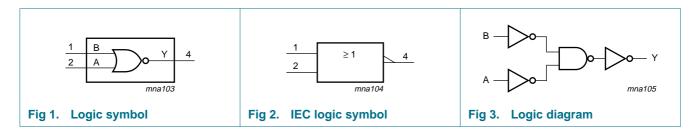
4. Marking

Table 2. Marking codes

Type number	Marking ^[1]
XC7SH02GW	fB
XC7SH02GV	f02

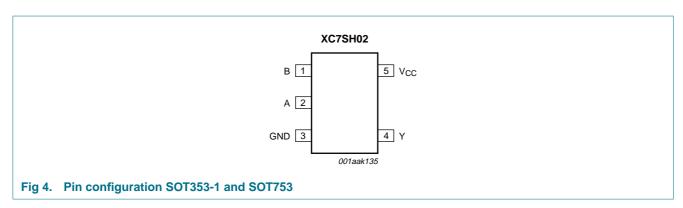
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input B
A	2	data input A
GND	3	ground (0 V)
Υ	4	data output Y
V_{CC}	5	supply voltage

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2-input NOR gate

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Inputs		Output
Α	В	Υ
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_{I}	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_{I} < -0.5 \text{ V}$	-20	-	mA
I_{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		–75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2]	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] For both TSSOP5 and SC-74A packages: above 87.5 $^{\circ}$ C the value of P_{tot} derates linearly with 4.0 mW/K.

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XC7SH02
2-input NOR gate

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	ns/V
		$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -50 \mu A$; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		I_{O} = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
II	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

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2-input NOR gate

11. Dynamic characteristics

Dynamic characteristics Table 8.

GND = 0 V. For test circuit see Figure 6.

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
				Min	Тур	Max	Min	Max	Min	Max	
t _{pd} propagation delay	A and B to Y; see Figure 5	<u>[1]</u>									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	[2]								
		C _L = 15 pF		-	4.4	7.9	1.0	9.5	1.0	10.5	ns
		C _L = 50 pF		-	6.3	11.4	1.0	13	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C _L = 15 pF		-	3.2	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.6	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$; $f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	18	-	-	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times f_i + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$$

 f_i = input frequency in MHz; f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

^[2] Typical values are measured at $V_{CC} = 3.3 \text{ V}$.

^[3] Typical values are measured at $V_{CC} = 5.0 \text{ V}$.

2-input NOR gate

12. Waveforms

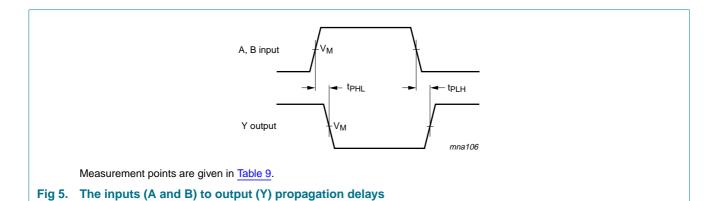
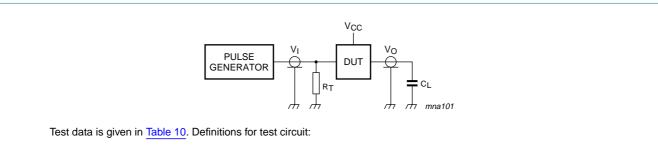


Table 9. Measurement point

Туре	Input	Output	
	V _I	V _M	V _M
XC7SH02	GND to V _{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

Fig 6. Load circuitry for switching times

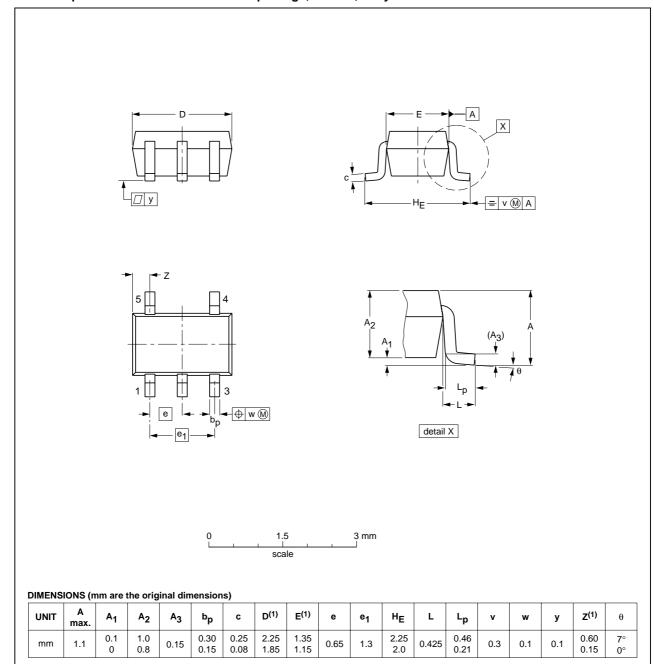
Table 10. Test data

Туре	Input		Load	Test	
	V _I	t _r , t _f	CL		
XC7SH02	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}	

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE REFERENCES					EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19	

Fig 7. Package outline SOT353-1 (TSSOP5)

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Plastic surface-mounted package; 5 leads

SOT753

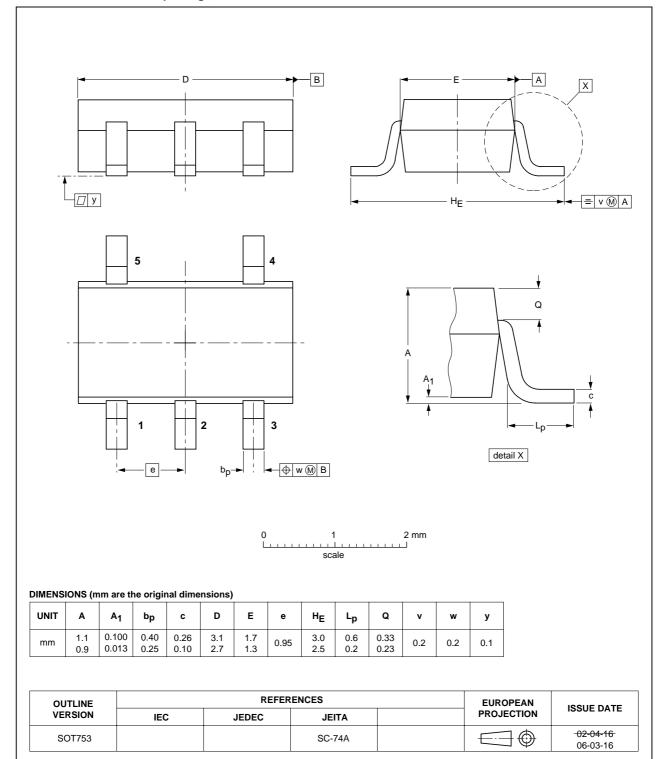


Fig 8. Package outline SOT753 (SC-74A)

Product data sheet

8 of 11

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XC7SH02
2-input NOR gate

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
XC7SH02_1	20090907	Product data sheet	-	-

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2-input NOR gate

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16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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XC7SH02 NXP Semiconductors

2-input NOR gate

18. Contents

1	General description
2	Features
3	Ordering information
4	Marking 2
5	Functional diagram 2
6	Pinning information 2
6.1	Pinning
6.2	Pin description 2
7	Functional description 3
8	Limiting values 3
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 5
12	Waveforms 6
13	Package outline
14	Abbreviations 9
15	Revision history 9
16	Legal information
16.1	Data sheet status
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks10
17	Contact information 10
18	Contents 11

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Date of release: 7 September 2009

Document identifier: XC7SH02_1